



HVGT High voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

### SHAPE DISPLAY:



### FEATURES:

1. High reliability design.
2. High voltage design.
3. High frequency .
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

### APPLICATIONS:

1. High voltage multiplier circuit
2. Electrostatic generator circuit .
3. General purpose high voltage rectifier.
4. Other.

### MECHANICAL DATA:

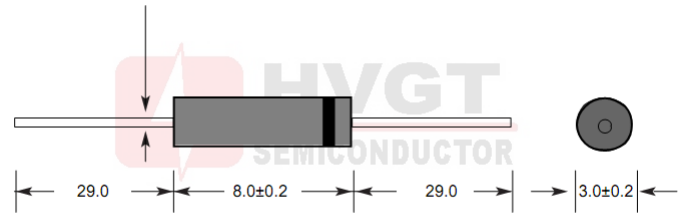
1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 0.26 grams (approx).

SIZE: (Unit:mm)

HVGT NAME: DO-308

### DO-308 Series

Lead Diameter 0.6±0.03



Unit:mm

### MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

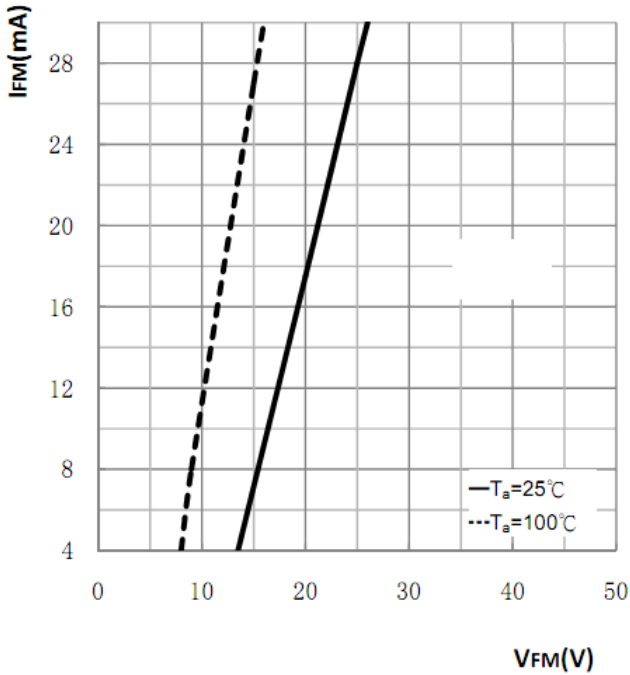
| Items                                | Symbols   | Condition                          | Data Value | Units       |
|--------------------------------------|-----------|------------------------------------|------------|-------------|
| Repetitive Peak Reverse Voltage      | $V_{RRM}$ | $T_a=25^{\circ}C$ ;                | 6.0        | kV          |
| Average Output Current               | $I_F$     | $T_a=25^{\circ}C$ ;Resistive Load  | 5.0        | mA          |
| Suege Current                        | $I_{FSM}$ | $T_a=25^{\circ}C$ ; 1/2 Sine(60Hz) | 0.5        | A           |
| Junction Temperature                 | $T_J$     |                                    | -40~+125   | $^{\circ}C$ |
| Allowable Operation Case Temperature | $T_C$     |                                    | 125        | $^{\circ}C$ |
| Storage Temperature                  | $T_{STG}$ |                                    | -40~+125   | $^{\circ}C$ |

### ELECTRICAL CHARACTERISTICS: $T_a=25^{\circ}C$ (Unless otherwise specified)

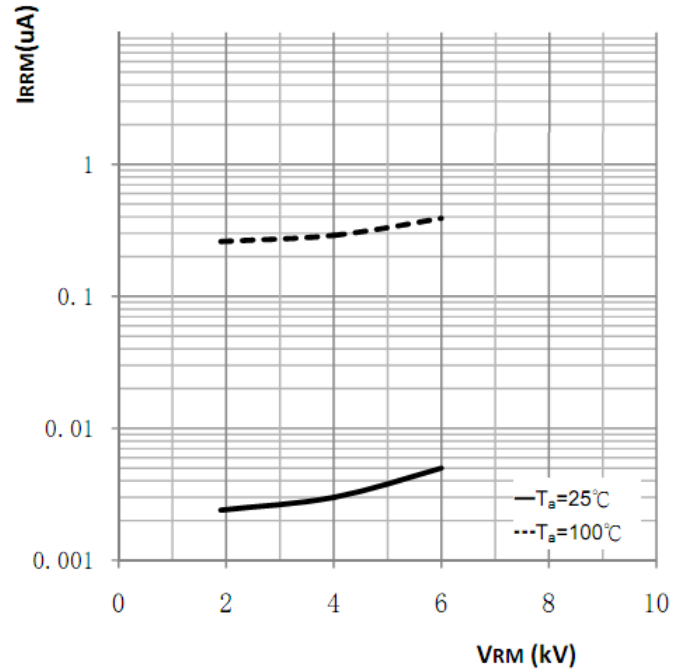
| Items                         | Symbols  | Condition   | Data value | Units   |
|-------------------------------|----------|---|------------|---------|
| Maximum Forward Voltage Drop  | $V_F$    | at $25^{\circ}C$ ; at $I_{F(AV)}$                                   | 25         | V       |
| Maximum Reverse Current       | $I_{R1}$ | at $25^{\circ}C$ ; at $V_{RRM}$                                     | 2.0        | $\mu A$ |
|                               | $I_{R2}$ | at $100^{\circ}C$ ; at $V_{RRM}$                                    | 5.0        | $\mu A$ |
| Maximum Reverse Recovery Time | $T_{RR}$ | at $25^{\circ}C$ ; $I_F=0.5I_R$ ; $I_R=I_{FAVM}$ ; $I_{RR}=0.25I_R$ | 80         | nS      |
| Junction Capacitance          | $C_J$    | at $25^{\circ}C$ ; $V_R=0V$ ; $f=1MHz$                              | 1.0        | pF      |



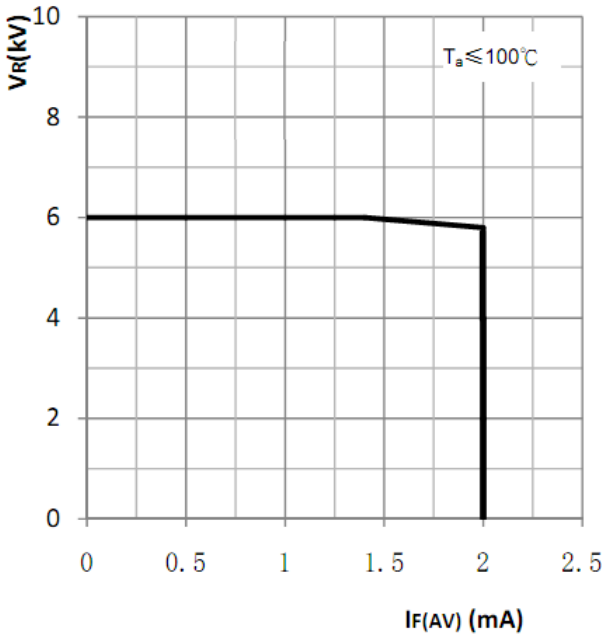
**Fig1**  
**Forward Characteristics**



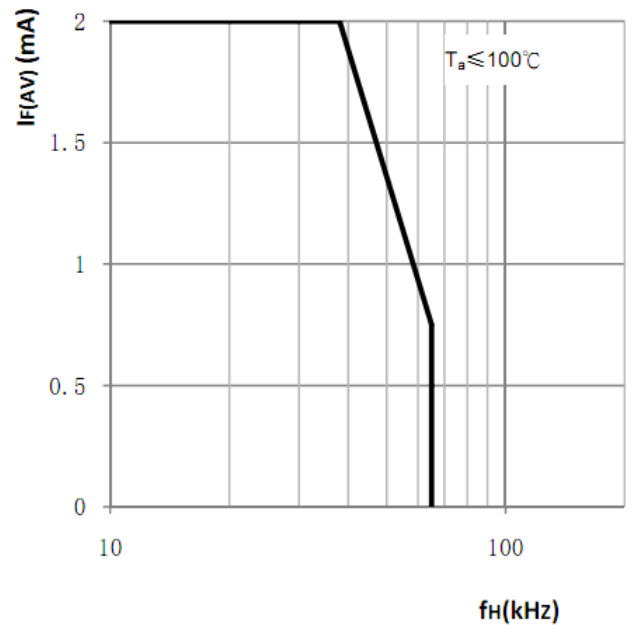
**Fig2**  
**Reverse Characteristics**



**Fig3**  
**VR-IF(AV) Curve**



**Fig4**  
**IF(AV)-fH Curve**



**Marking**

Type

ESJA54-06

Code

Cathode Mark

